

Title (en)  
SEMICONDUCTOR DEVICE HAVING AN INTERCONNECTION PATTERN

Publication  
**EP 0083816 B1 19870325 (EN)**

Application  
**EP 82201629 A 19821220**

Priority  
NL 8105920 A 19811231

Abstract (en)  
[origin: EP0083816A1] With the aid of anisotropic etching techniques, such as plasma etching and reactive ion etching, inter-connection patterns can be obtained having accurately defined rims. According to the invention, these rims are provided inter alia at the area of contacts to be formed. The contacting zone thus formed, which has an accurately defined form, can be manufactured with rims of, for example, a refractory metal or polycrystalline silicon. In the latter case, a semiconductor zone (emitter zone, base contact zone, source, drain etc.) can be formed through the polycrystalline silicon in the subjacent semiconductor body. In this manner, very small structures can be obtained, whilst moreover different kinds of transistors can be manufactured in the same semiconductor body.

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IPC 8 full level  
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CPC (source: EP US)  
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Citation (examination)  
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• US 3066052 A 19621127 - HOWARD BRIAN T  
• IBM TECHNICAL DISCLOSURE BULLETIN, vol. 21, no. 12, May 1979, New York, USA H.H. BERGER et al.: "Cross-coupled flip-flop transistors with stacked interconnection lines", page 4886

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